

Silizium-PIN-Fotodiode mit sehr kurzer Schaltzeit Silicon PIN Photodiode With Very Short Switching Time

SFH 216



Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 350 nm bis 1100 nm
- Kurze Schaltzeit (typ. 5 ns)
- Hermetisch dichte Metallbauform (TO-18)

Anwendungen

- Schneller optischer Empfänger mit großer Modulationsbandbreite für Lichtgriffel

Features

- Especially suitable for applications from 350 nm to 1100 nm
- Short switching time (typ. 5 ns)
- Hermetically sealed metal package (TO-18)

Applications

- Optical sensor of high modulation bandwidth for light pens

Typ Type	Bestellnummer Ordering Code
SFH 216	Q62702-P936

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 125	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ($t \leq 3$ s)	T_S	230	°C
Sperrspannung Reverse voltage	V_R	50	V
Verlustleistung, $T_A = 25$ °C Total power dissipation	P_{tot}	250	mW

Kennwerte ($T_A = 25$ °C, Normlicht A, $T = 2856$ K)
Characteristics ($T_A = 25$ °C, standard light A, $T = 2856$ K)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotoempfindlichkeit, $V_R = 5$ V Spectral sensitivity	S	50 (≥ 35)	nA/lx
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S \max}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{\max} Spectral range of sensitivity $S = 10\%$ of S_{\max}	λ	350 ... 1150	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	1	mm ²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	1 × 1	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	4.2 ... 5.0	mm
Halbwinkel Half angle	φ	± 12	Grad deg.
Dunkelstrom, $V_R = 20$ V Dark current	I_R	1 (≤ 5)	nA
Spektrale Fotoempfindlichkeit, $\lambda = 850$ nm Spectral sensitivity	S_λ	0.55	A/W

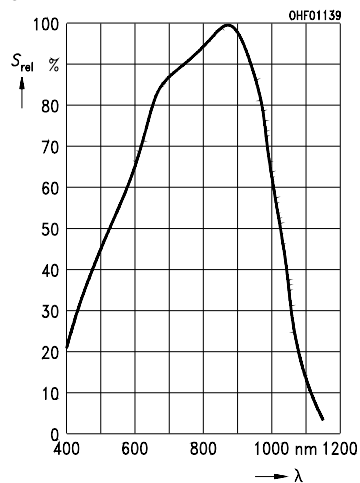
Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)

Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$) (cont'd)

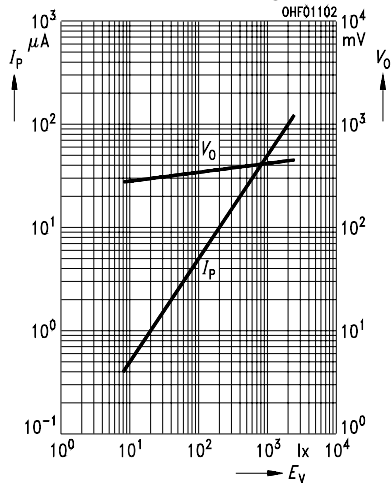
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Quantenausbeute, $\lambda = 850\text{ nm}$ Quantum yield	η	0.80	<u>Electrons</u> Photon
Leerlaufspannung, $E_V = 1000\text{ lx}$ Open-circuit voltage	V_O	410 (≥ 350)	mV
Kurzschlußstrom, $E_V = 1000\text{ lx}$ Short-circuit current	I_{SC}	50	μA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\ \Omega$; $V_R = 20\text{ V}$; $\lambda = 850\text{ nm}$; $I_p = 800\ \mu\text{A}$	t_r, t_f	5	ns
Durchlaßspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.3	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	11	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	-2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC}	TC_I	0.2	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 20\text{ V}$, $\lambda = 850\text{ nm}$	NEP	3.3×10^{-14}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 20\text{ V}$, $\lambda = 850\text{ nm}$ Detection limit	D^*	3.1×10^{12}	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

Relative Spectral Sensitivity

$S_{rel} = f(\lambda)$

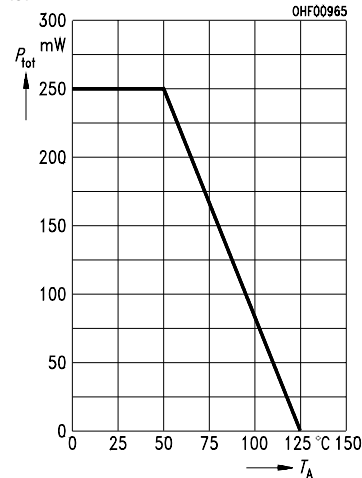


**Photocurrent $I_P = f(E_V), V_R = 5 V$
Open-Circuit Voltage $V_O = f(E_V)$**



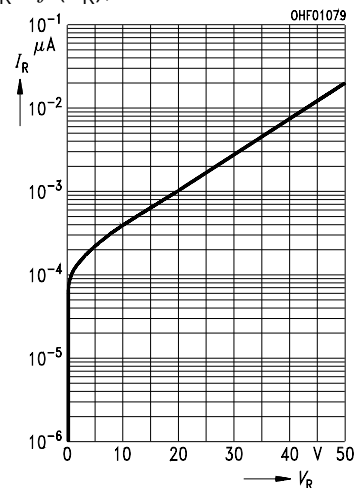
Total Power Dissipation

$P_{tot} = f(T_A)$



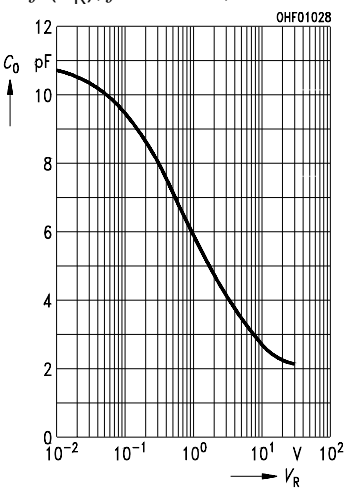
Dark Current

$I_R = f(V_R), E = 0$



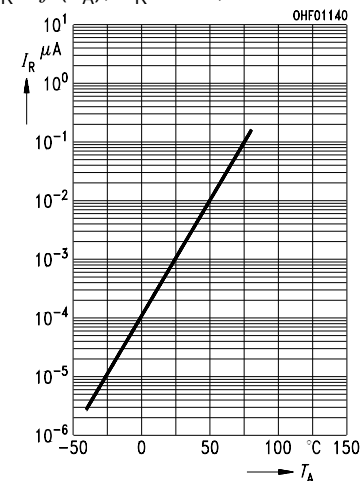
Capacitance

$C = f(V_R), f = 1 MHz, E = 0$



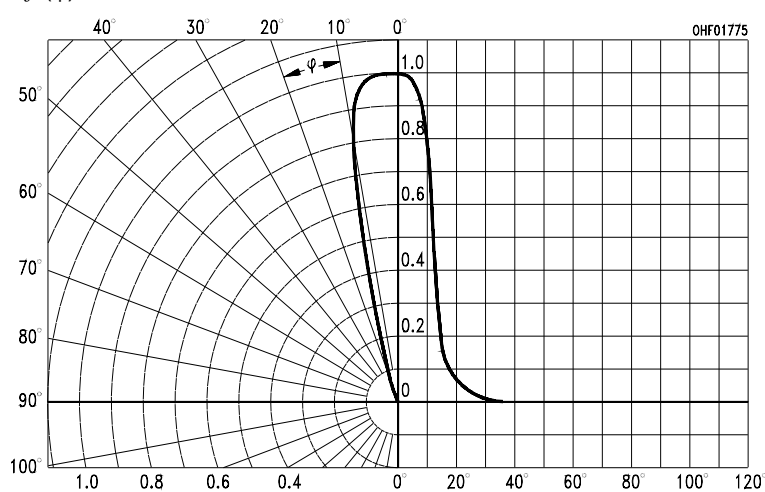
Dark Current

$I_R = f(T_A), V_R = 1 V, E = 0$

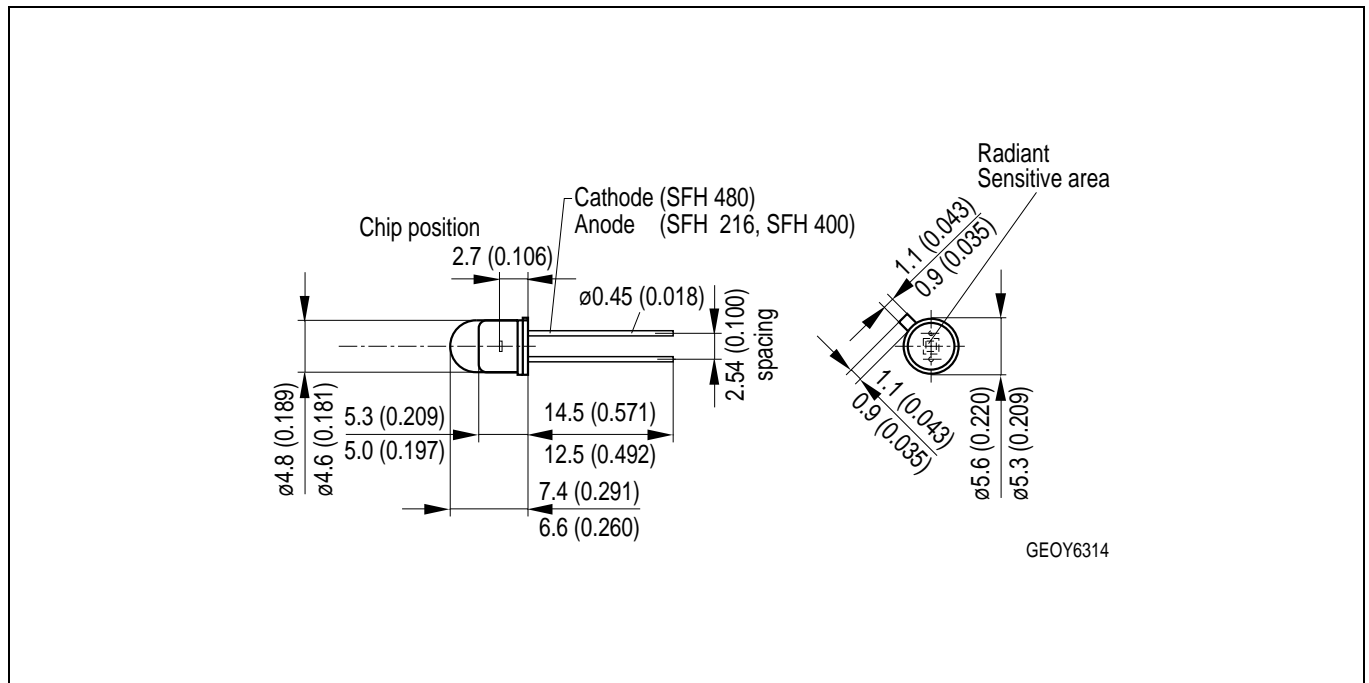


Directional Characteristics

$S_{rel} = f(\varphi)$



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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